Bipolar Transistor



RoHS Compliant

Description

Switchmode Series NPN Power Transistors is designed for use in high-voltage,high-speed, power switching regulators, converters, inverters, motor control system application



Features

- Collector-Emitter Sustaining Voltage-VCEO(SUS) = 400 V (Min)
- Collector-Emitter Saturation Voltage -VCE(sat) =1.5 V (Max.) @ Ic = 10 A
- Switching Time-t_f = 0.8 us (Max.)@ Ic =10 A

Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-Emitter Voltage	Vceo	400		
Collector-Emitter Voltage (V _{Be} =-2.5V)	Vcex	850	V	
Emitter-Base Voltage	VEBO	7		
Collector Current - Continuous -Peak	Ic I см	15 30 A		
Base Current	Ів	4		
Total Power Dissipation @Tc = 25°C Derate above 25°C	Po	150 1	W W°C	
Operating and Storage Junction Temperature Range	Тյ,Тsтg	-65 to +175	°C	

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance Junction to Case	Rejc	1	°C/W

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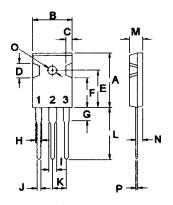


Electrical Characteristics (Tc = 25°C unless otherwise specified

	Parameter	Symbol	Min.	Max.	Unit
Off Characteristics					
Collector-Emitter Su Ic= 200mA, IB=0, L=		Vceo(sus)	400 450	-	V
Collector Cut-off Cur VCE= VCEX, VBE = -2. VCE= VCEX, VBE = -2.	5V)	lcex		0.2 2	
Collector Cut-off Cur VCE= VCEX, RBE < 10 VCE= VCEX, RBE < 10	Ω)	Icer		0.5 4	mA
Emitter Cut-off Curre V _{EB} =5V, I _C =0	ent	ІЕВО		1	
On Characteristics (1)					
Collector-Emitter Sa (Ic= 10A, IB=2A) (Ic= 15A, IB=3A)	turation Voltage	VCE(SAT)		1.5 5	V
Base-Emitter Saturation Voltage (Ic= 10A, Iв=2A)		VBE(SAT)	-	1.6	
Switching Characteristics					
Turn On Time		ton	1		
Storage Time	Ic= 10A, I _{B1} = 2A I _{B2} = -2.0A V _{CC} = 150V	ts		3 us	
Fall Time	V 00 100V	tf		0.8	

(1) Pulse Test: Pulse width = 300, us, Duty Cycle ≤2%

Dimensions



PIN 1. Base

2. Collector

3. Emitter

	450	FIGURE -1 POWER DERATING					
	150						
Ę	125		<u> </u>			 -	
P _D , POWER DISSIPATION(WATTS)	100						
6	100						
<u>8</u>	75						
器	50						
Ä	50						
ğ	25					>	
~ °	0		<u></u>				
	() 2	25 5		75 10 MPERAT		50 175

Dim	Min.	Max.
Α	20.63	22.38
В	15.38	16.2
С	1.9	2.7
D	5.1	6.1
Е	14.81	15.22
F	11.72	12.84
G	4.2	4.5
Н	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.5	21.5
М	4.68	5.36
N	2.4	2.8
0	3.25	3.65
Р	0.55	0.7

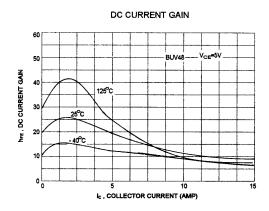
Dimensions : Millimetres

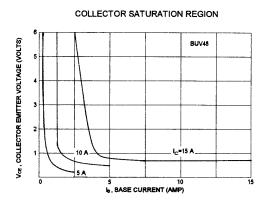
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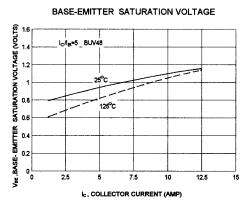


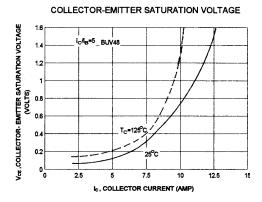
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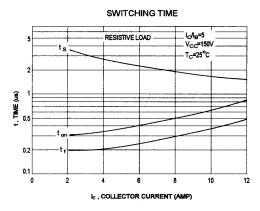


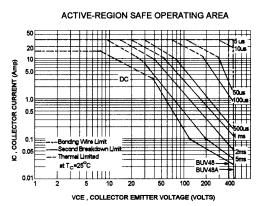












Part Number Table

Description	Part Number
Transistor, NPN, 15A, 400V, 150W, TO-247	MP008586

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